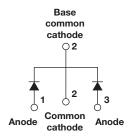


HEXFRED®, Ultrafast Soft Recovery Diode, 2 x 15 A



D²PAK (TO-263AB)



PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 15 A					
V_{R}	600 V					
V _F at I _F	1.2 V					
t _{rr} (typ.)	19 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Common cathode					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C





COMPLIANT

HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA30TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A per leg continuous current, the VS-HFA30TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V _R		600	V				
Maximum continuous forward current per leg	I_	T _C = 100 °C	15					
per device	IF	1C = 100 C	30	Α				
Single pulse forward current	I _{FSM}		150	A				
Maximum repetitive forward current	I _{FRM}		60					
Maximum nawar dissination	P _D	T _C = 25 °C 74		°C				
Maximum power dissipation		T _C = 100 °C	29	C				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	W				





ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	600	-	-			
		I _F = 15 A	See fig. 1	-	1.3	1.7	V	
Maximum forward voltage	V_{FM}	I _F = 30 A		-	1.5	2.0		
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6		
Maximum reverse	1	V _R = V _R rated	$V_R = V_R$ rated		1.0	10		
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated See fig. 2		-	400	1000	μΑ	
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	25	50	pF	
Series inductance	L _S	Measured lead to lead 5 mm from p	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/μs, V _R = 30 V	-	19	-			
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	42	60	ns		
300 lig. 0, 10	t _{rr2}	T _J = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	70	90]		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.0	6.0	- A		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	80	180			
See fig. 7	Q _{rr2}	T _J = 125 °C		-	220	450	IIC		
Peak rate of fall of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-	A/μs		
current during t _b See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-			

THERMAL - MECHA	THERMAL - MECHANICAL SPECIFICATIONS PER LEG								
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS					UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Junction to case, single leg conducting	R _{th,JC}		-	-	1.7				
Junction to case, both legs conducting	PthJC		-	-	0.85	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80				
Weight			-	2.0	-	g			
vveignt			-	0.07	-	OZ.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style D ² PAK (TO-263AB)		HFA30TA60CS					

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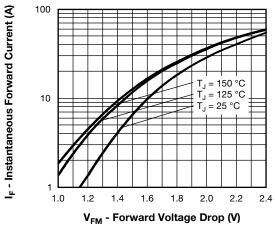


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

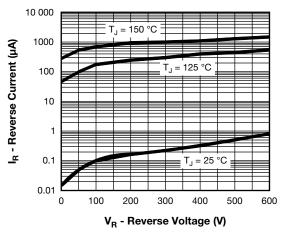


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

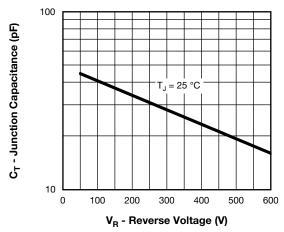


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

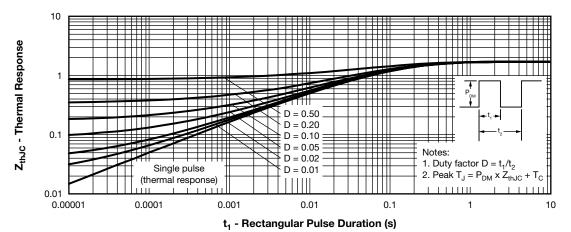


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

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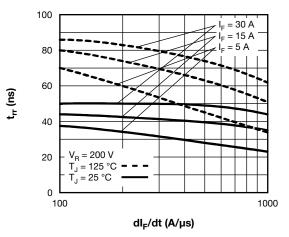


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

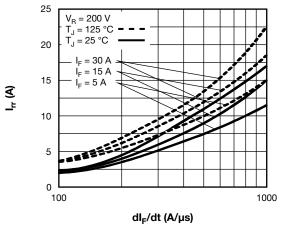


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

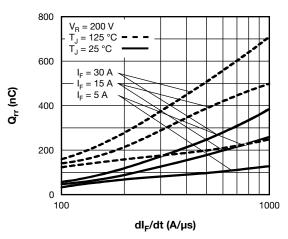


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

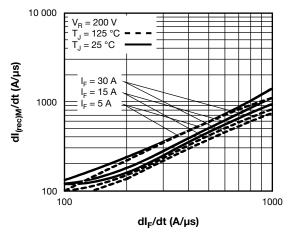
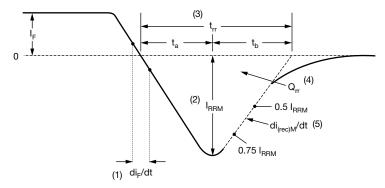


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

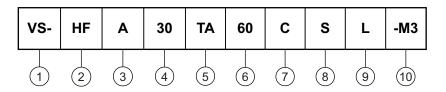
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

- Process designator: A = electron irradiated

4 - Current rating (30 = 30 A)

Fackage outline (TA = TO-220, 3 leads)

6 - Voltage rating (60 = 600 V)

- Circuit configuration (C = common cathode)

8 - $S = D^2PAK (TO-263AB)$

9 - • None = tube

• L = tape and reel (left oriented)

• R = tape and reel (right oriented)

10 - Environmental digit

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA30TA60CS-M3	50	1000	Antistatic plastic tube					
VS-HFA30TA60CSR-M3	800	800	13" diameter reel					
VS-HFA30TA60CSL-M3	800	800	13" diameter reel					

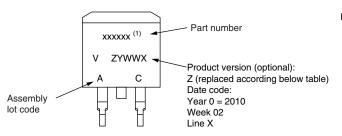
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



Part Marking Information

Vishay Semiconductors

D²PAK



Example: This is a xxxxxx ⁽¹⁾ with assembly lot code AC, assembled on WW 02, 2010

Note

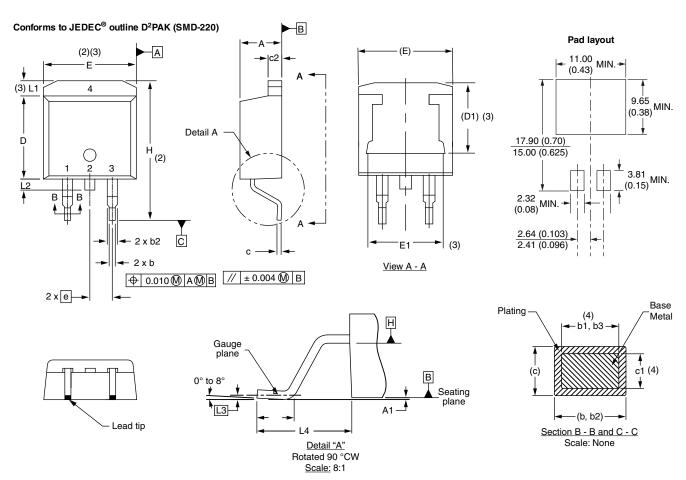
(1) If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION				
А	Termination lead (Pb)-free				
В	Totally lead (Pb)-free				
E	RoHS-compliant and termination lead (Pb)-free				
F	RoHS-compliant and totally lead (Pb)-free				
M	Halogen-free, RoHS-compliant, and termination lead (Pb)-free				
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free				
G Green					



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

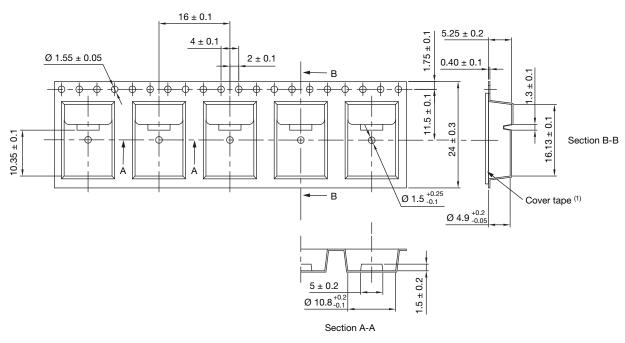
Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

D²PAK (TO-263AB)

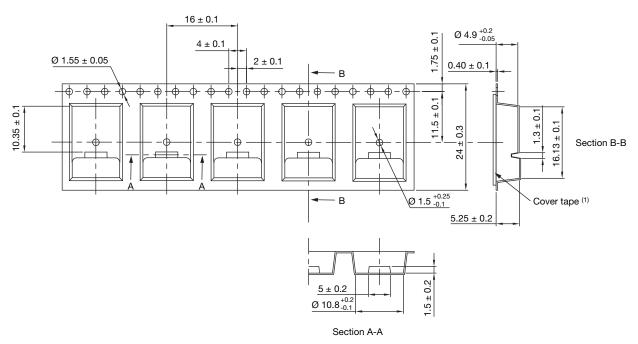
CARRIER TAPE FOR TAPE AND REEL LEFT in millimeters



Note

(1) For dimensions, see next pages

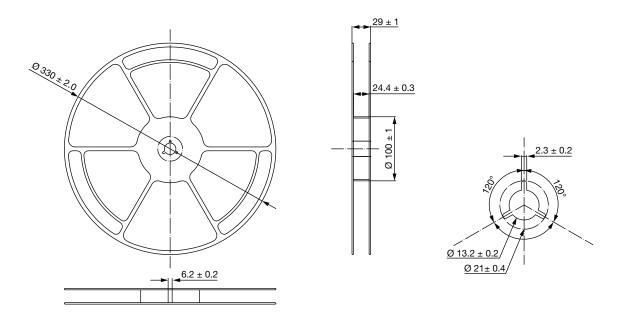
CARRIER TAPE FOR TAPE AND REEL RIGHT in millimeters



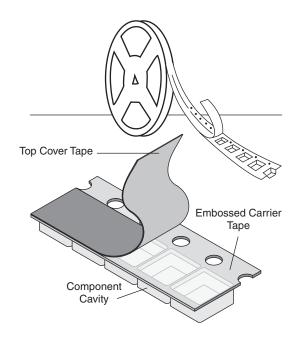
Note

(1) For dimensions, see next pages

REEL FOR CARRIER TAPE in millimeters



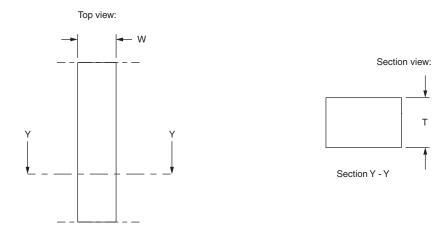
CARRIER TAPE AND REEL PACKAGING D²PAK (TO-263AB)



Packaging Information

Vishay Semiconductors

COVER TAPE FOR CARRIER TAPE in millimeters



APPLICATION	COVER TAPE WIDTH W	COVER TAPE THICKNESS T	CARRIER TAPE WIDTH	MATERIAL
D ² PAK (TO-263AB)	21.3 ± 0.1	0.060 ± 0.01	24	Antistatic/treated/transparent/polyester



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